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BTA208X-800E

3Q Hi-Com Triac

Rev. 07 — 25 January 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- Electronic thermostats
- General purpose motor controls

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	-	65	A
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{h}} \leq 73\text{ }^{\circ}\text{C}$; see Figure 3 ; see Figure 1 ; see Figure 2	-	-	8	A

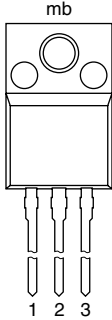


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; see Figure 7	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; see Figure 7	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; see Figure 7	-	-	10	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

SOT186A (TO-220F)

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BTA208X-800E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_h \leq 73^\circ\text{C}$; see Figure 3 ; see Figure 1 ; see Figure 2	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{J(init)}} = 25^\circ\text{C}$; $t_p = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	65	A
		full sine wave; $T_{\text{J(init)}} = 25^\circ\text{C}$; $t_p = 16.7\text{ ms}$	-	71	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	21	A^2s
dI_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 0.2\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^\circ\text{C}$
T_{J}	junction temperature		-	125	$^\circ\text{C}$

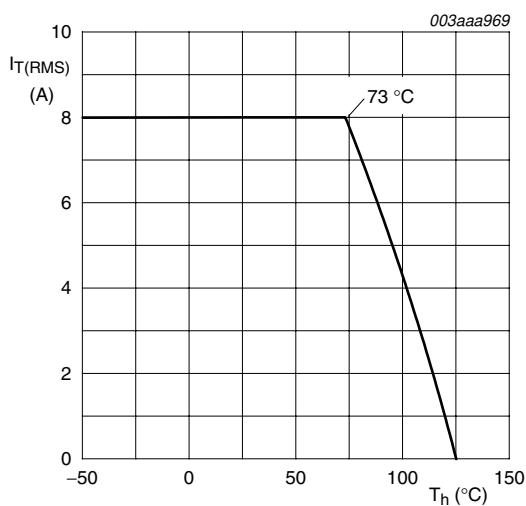
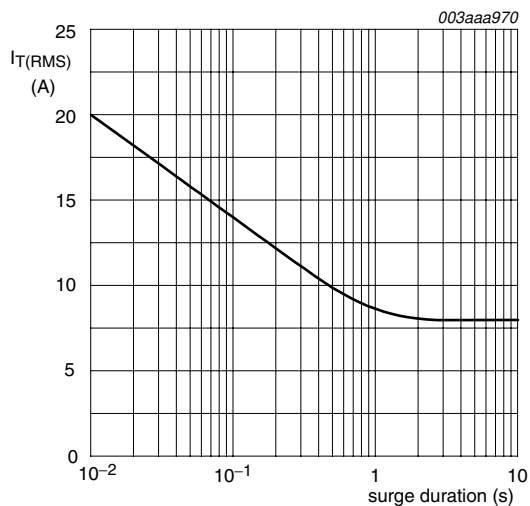


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values



$f = 50\text{ Hz}$; $T_h = 73^\circ\text{C}$

Fig 2. RMS on-state current as a function of surge duration; maximum values

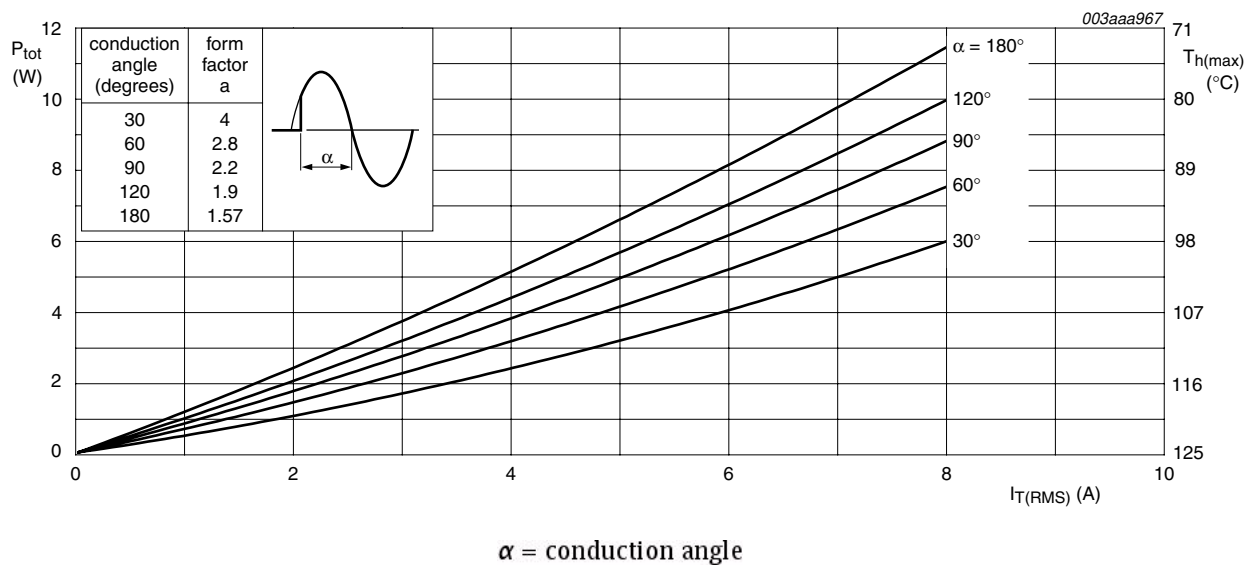


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

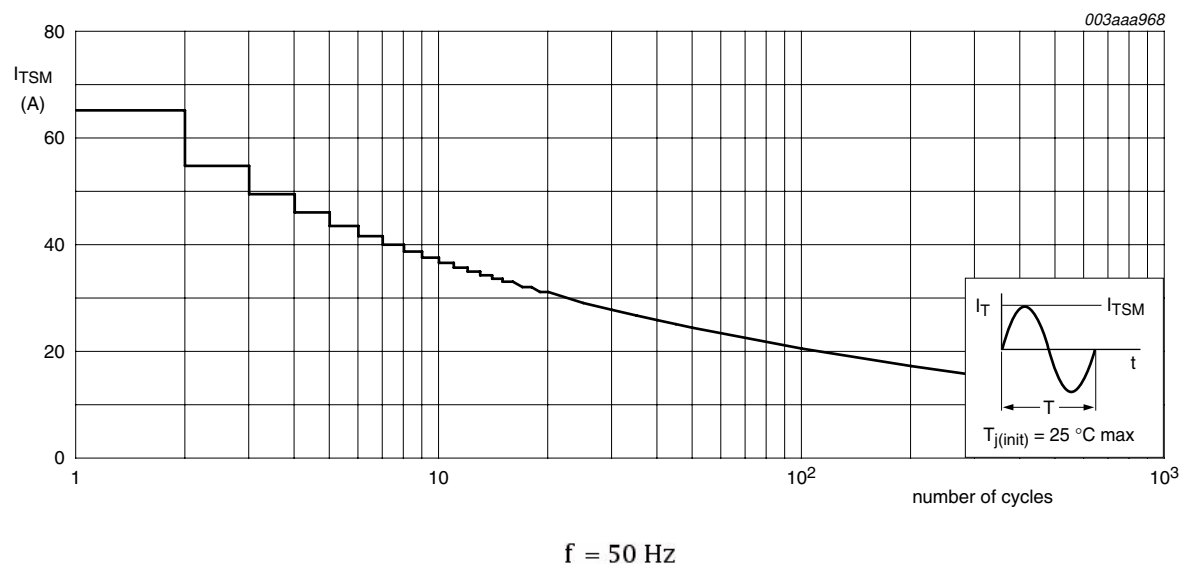


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

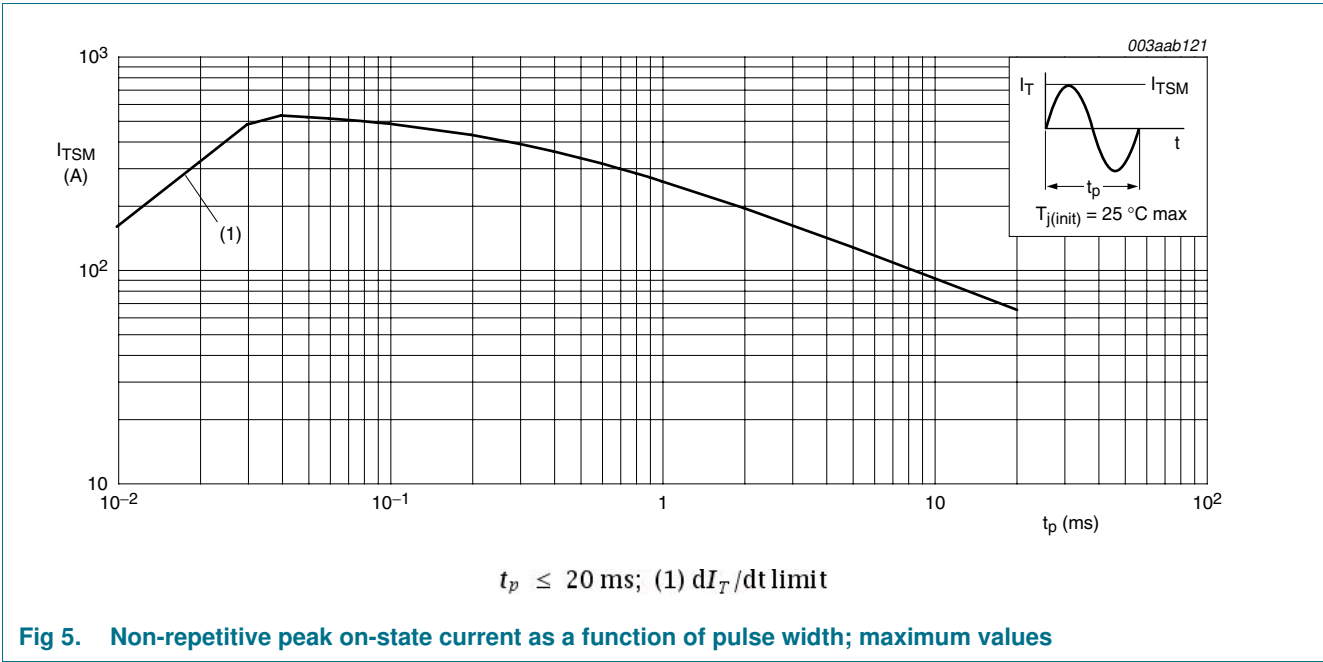
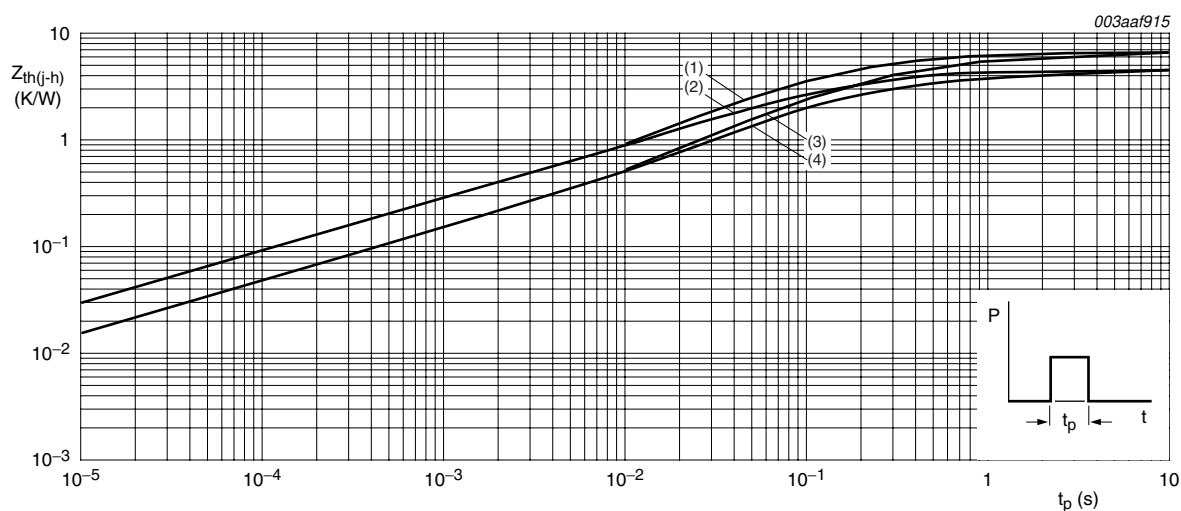


Fig 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T _h = 25 °C	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink ; f = 1 MHz; T _h = 25 °C	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 8	-	-	12	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	18	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	12	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; see Figure 9	-	-	12	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_j = 25\text{ °C}$; see Figure 10	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; see Figure 11	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.25	0.4	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 110\text{ °C}$; exponential waveform; gate open circuit	60	-	-	V/ μ s
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit; see Figure 12	5	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 0.1\text{ V}/\mu\text{s}$; gate open circuit; see Figure 12	10	-	-	A/ms

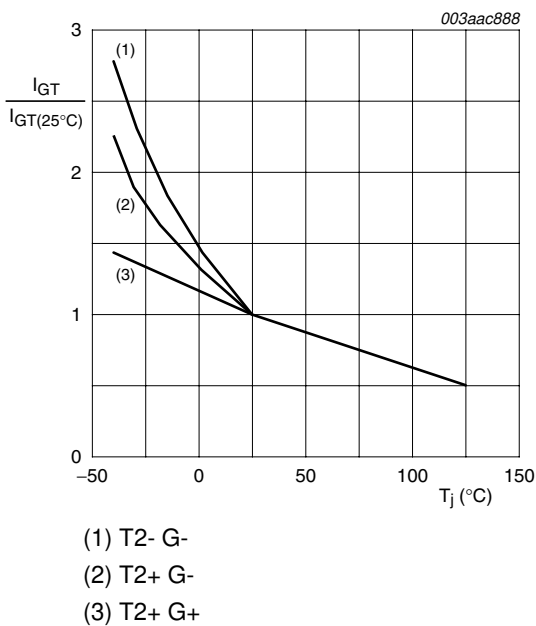


Fig 7. Normalized gate trigger current as a function of junction temperature

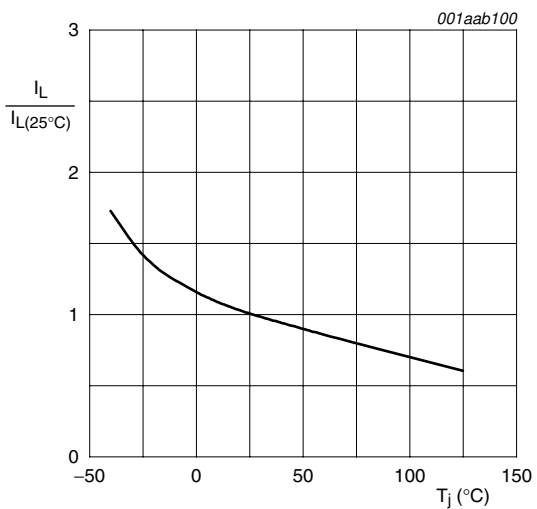


Fig 8. Normalized latching current as a function of junction temperature

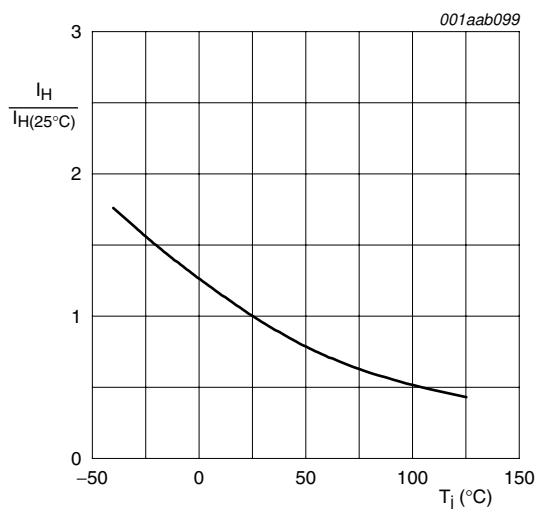


Fig 9. Normalized holding current as a function of junction temperature

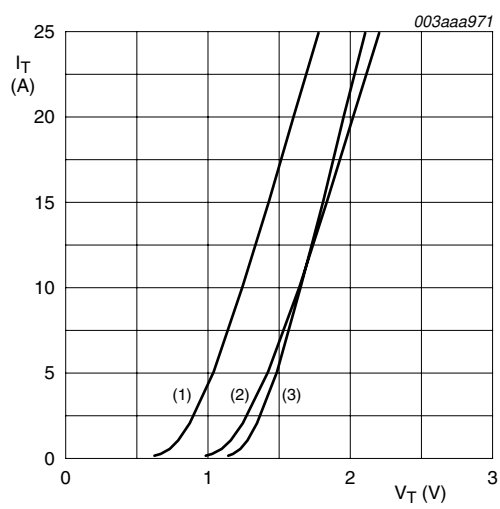
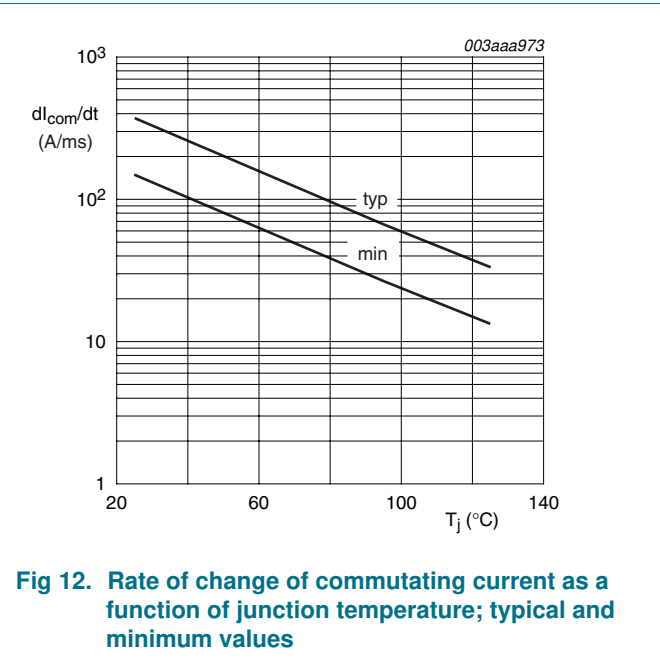
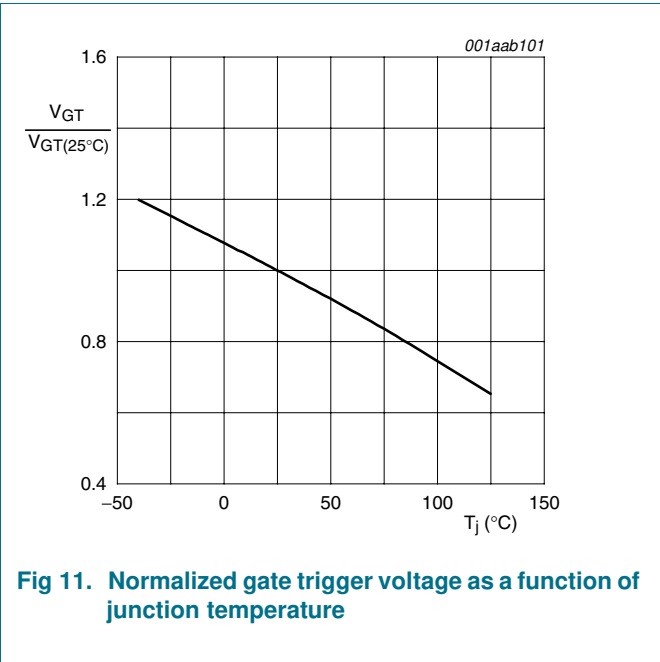


Fig 10. On-state current as a function of on-state voltage



8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

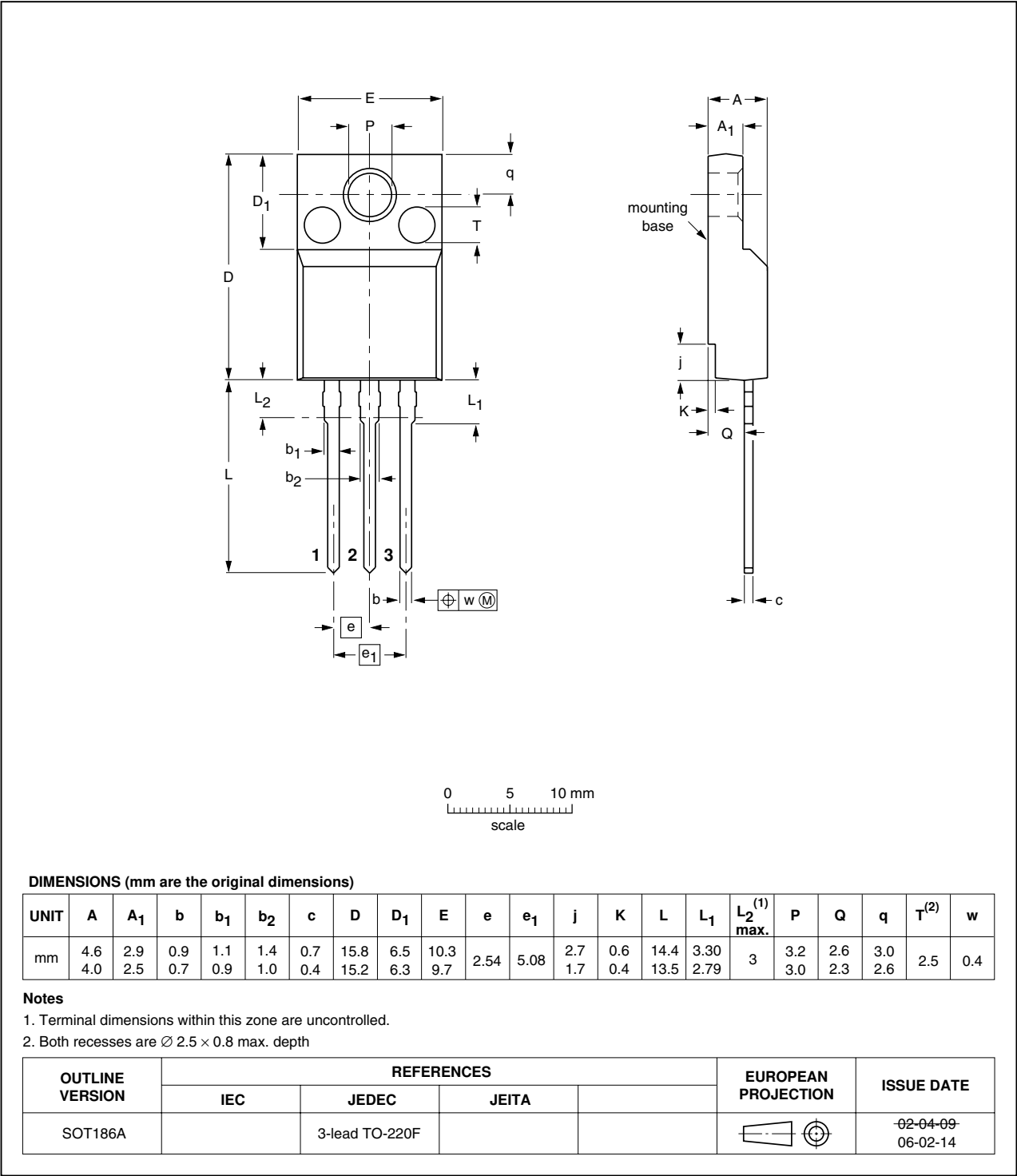


Fig 13. Package outline SOT186A (TO-220F)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA208X-800E v.7	20110125	Product data sheet	-	BTA208X-800E v.6
Modifications: • Various changes to content.				
BTA208X-800E v.6	20101109	Product data sheet	-	BTA208X_SERIES_D_E_F_5

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Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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